Ref	Hits	Search Query	DBs	Default	Plurals	Time Stamp
#				Operator		2007/2010
L1	38	finger with overlap\$4 and test\$4 with align\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:20
L2	58	finger with overlap\$4 and measur\$4 with align\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:21
L3	256	electrode with overlap\$4 and measur\$4 with align\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:21
L4	111	electrode with overlap\$4 and measur\$4 with align\$4 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:29
L5	31	electrode with overlap\$4 and offset and measur\$4 with align\$4 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:27
L6	17	5 and capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:28
L7	80	electrode with overlap\$4 and test\$4 with align\$4 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:29
L8	48	electrode with overlap\$4 and test\$4 with align\$4 and semiconductor and offset	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:30

L9	41	electrode with overlap\$4 and test\$4 with align\$4 and semiconductor and offset and capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:31
L10	0	finger with overlap\$4 and test\$4 with align\$4 and semiconductor and offset and capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:31
L11	92	finger with overlap\$4 with ((horizontal with vertical) or (lateral with vertical))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:33
L12	0	finger with overlap\$4 with ((horizontal with vertical) or (lateral with vertical)) and ((measur\$4 or test\$4) with align\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:33

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	239	438/21.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:14
L2	8	1 and electrode with overlap\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:16
L3	730	overlap\$6 and misalignment and test\$4 and finger	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:18
L4	92	overlap\$6 and misalignment and test\$4 and finger and gate and active adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:19
L5	0	4 and fourth with finger	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:19
L6	3	4 and second with finger	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:27
L7	48	electrode with overlap\$4 and test\$4 with align\$4 and semiconductor and offset	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:22
L8	15	capacitance with measur\$4 with misalign\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:24

L9	7	capacitance with test\$4 with misalign\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:24
L10	0	("2004/0124412").URPN.	USPAT	OR	OFF	2005/09/30 17:25
L11	0	257/48.ccls. and capacitance with test\$4 with misalign\$4	USPAT	OR	OFF	2005/09/30 17:26
L12	738	257/48.ccls.	USPAT	OR	OFF	2005/09/30 17:26
L13	0	257/48.ccls. and overlap\$4 with cpacitance and misalign\$4	USPAT	OR	OFF	2005/09/30 17:26
L14	850	438/30.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:27
L15	21	14 and capacitance and misalign\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 17:27